

## **isc Silicon NPN Power Transistor**

# BUX25

### DESCRIPTION

- · Low Collector Saturation Voltage-
- High Switching Speed
- High Current Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

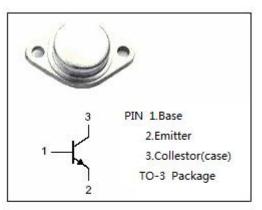
• Desinged for use in switching and linear applications in military and industrial equipment.

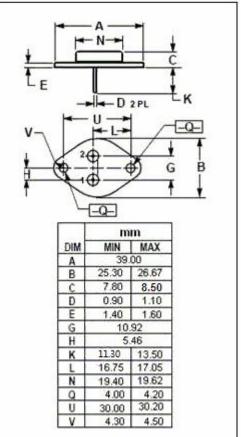
#### Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	500	V
VCEO	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	15	А
Ісм	Collector Current-Peak	20	А
I <sub>B</sub>	Base Current-Continuous	3	А
Pc	Collector Power Dissipation @Tc=25°C	350	W
Tj	Junction Temperature	200	°C
T <sub>stg</sub>	Storage Temperature Range	-65~200	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.5	°C/W







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### **ELECTRICAL CHARACTERISTICS**

 $T_c=25^{\circ}C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	500			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7			V
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.8A			0.6	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A ;I <sub>B</sub> = 1.6A			1.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A ;I <sub>B</sub> = 1.6A			1.5	v
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 400V; I <sub>B</sub> = 0			3.0	mA
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB}$ = 500V; I <sub>E</sub> = 0 $V_{CB}$ =500V; I <sub>E</sub> = 0;T <sub>C</sub> =125°C			3.0 12.0	mA
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 4V	15		60	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 8A ; V <sub>CE</sub> = 4V	8			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 2A; V <sub>CE</sub> = 15V, f <sub>test</sub> = 10MHz	8			MHz

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